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Superconductivity in Semiconductor Structures: the Excitonic Mechanism

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We study theoretically the effect of the fermion and boson densities on the superconductivity transition critical temperature (T_c) of a two dimensional electron gas (2DEG), where superconductivity is mediated by a Bose-Einstein condensate of exciton-polaritons. The critical temperature is found to increase with the boson density, but surprisingly it decreases with the 2DEG density increase. This makes doped semiconductor structures with shallow Fermi energies better adapted for observation of the exciton-induced superconductivity than metallic layers. For the realistic GaAs-based microcavities containing-doped and neutral quantum wells we estimate T_c as close to 50K. Superconductivity is suppressed by magnetic fields of the order of 4T due to the Fermi surface renormalisation.

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High temperature superconductivity (HTSC) has been desperately searched for during decades since the appearance of the seminal work of Bardeen-Cooper-Schrieffer (BCS) [1] in the early 50s. Among many different paths physicist have tried to achieve it, the excitonic mechanism of superconductivity (SC) deserves a particular attention[2–4]. According to Ginsburg [5, 6], excitons are expected to be suitable for realization of HTSC because the characteristic energy above which the electron attraction mediated by excitons vanishes is several orders of magnitude larger than the Debye energy limiting the attraction mediated by phonons.

Despite optimistic expectations, to the best of our knowledge, the exciton mechanism of SC has never worked until now, most likely due the reduced retardation effect[4, 7]. Phonons in the BCS model are very slow compared to electrons on the Fermi surface. Hence there is a strong retardation effect in phonon-mediated electron-electron attraction, so that the size of a Cooper pair is very large (of the order of 100nm), and the Coulomb repulsion can be neglected at such distances. In contrast, an exciton is a very fast quasi-particle once it is accelerated to the wave-vectors comparable with the Fermi wave-vector in a metal. Therefore the replacement of phonons by excitons leads to the loss of retardation and the smaller sizes of Cooper pairs, that is why the Coulomb repulsion starts playing an important role. In realistic multilayer structures the Coulomb repulsion appears to be stronger than the exciton-mediated attraction so that Cooper pairs cannot be formed. In literature [8, 9] one find reports on layered metal-insulator structures where SC at 50K in layered metal-insulator structures, nevertheless there is still no evidence that the excitonic mechanism is responsible for this effect.

Recently, the novel mechanism to achieve superconductivity mediated by exciton-polaritons has been proposed in references [10, 11]. Exciton-polaritons are quasiparticles that arise due to the strong coupling of excitons with light. Particularly interesting exciton-polariton related phenomena have been observed in semiconductor quantum wells (QW) embedded in microcavity[12, 13]. Bose-Einstein condensation of cavity exciton-polaritons at room temperature has been observed [14–17], making the exciton-polariton a promising boson to bind the Cooper pairs at high temperatures. Moreover, it has been proved that the strength of electron-electron interactions mediated by a condensate of exciton-polaritons can be controlled optically.

The systems considered previously in references [10, 11] consist of microcavities where free electrons in a thin layer interact with contained in adjacent semiconductor layer exciton-polaritons. Both layers are brought sufficiently close to each other to assure efficient coupling between the electrons and exciton-polaritons. In this way, phonons are replaced by excitations of an exciton-polariton condensate providing exciton-mediated attraction of free electrons. While the retardation effect characteristic of the weak-coupling BCS model is essentially suppressed also in this regime, the exciton-mediated attraction appears to be strong enough to overcome the Coulomb repulsion for Cooper pairs of a characteristic size of 10 nm. In comparison to the mechanism considered by Bardeen [1] and Ginzburg [5, 6], electron-electron attraction mediated by excitons is much stronger in the presence of the exciton-polariton bosonic condensate for two reasons: first, the exchange energy needed for creation of an excited state of the condensate is much smaller than the energy needed to create a virtual exciton. Second, the exciton-electron interaction strength increases proportionally to the occupation number of the condensate. This exciton-polariton mechanism of superconductivity was studied theoretically in a model struc-

ture where the electron-electron attraction potential was calculated and then substituted into the gap equation that yielded the critical temperature of the superconductivity phase transition. The proof of concept calculation showed a high potentiality of the excitonic mechanism of SC.

In order to proceed with the experimental verifications of this prediction, several issues still need to be clarified. Namely, it has been unclear how the concentration of electrons influences the T_c and what structure is the most appropriate for experimental observation of the predicted effect: one where the metallic layer is put in contact with the semiconductor, or an entirely semiconductor multilayer structure containing doped and undoped QWs.

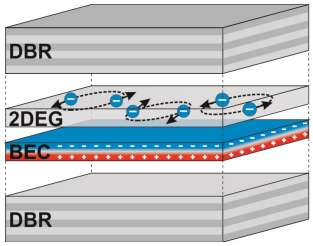

FIG. 1: The scheme of the model microcavity structure with an n-dopped QW interacting with an exciton-polariton BEC localized in an adjacent QW.

In this Letter, we analyse the behaviour of superconducting gap and T_c as a function of exciton-polariton and electron concentrations and conclude on the most convenient structure design for observation of the exciton-mediated SC.

The system we study is a microcavity where an electron gas confined to a quantum well (2DEG) interacts with a polariton condensate localized in an adjacent semiconductor QW, as shown in Fig.1. The microscopic Hamiltonian that describes this system is derived in ref.[11]. Here we only need the expression for the reduced Hamiltonian that appears after the Bogoliubov transformation and deacribes the coupling of electrons via excitations of a polariton condensate, so-called bogolons:

$$H = \sum_{\mathbf{k}} E_{el}(\mathbf{k})\sigma^{\dagger}_{\mathbf{k}}\sigma_{\mathbf{k}} + \sum_{\mathbf{k}} E_{bog}(\mathbf{k})b^{\dagger}_{\mathbf{k}}b_{\mathbf{k}} + H_c + \sum_{\mathbf{k},\mathbf{q}} M(\mathbf{q})\sigma^{\dagger}_{\mathbf{k}}\sigma_{\mathbf{k}+\mathbf{q}}(b^{\dagger}_{-\mathbf{q}} + b_{\mathbf{q}}). \quad (1)$$

Here E_{el} is the free electron energy, the bogolon dispersion is given by the formula:

$$E_{bog}(\mathbf{k}) = \sqrt{\tilde{E}_{pol}(\mathbf{k})(\tilde{E}_{pol}(\mathbf{k}) + 2UN_0A)} \quad (2)$$

where $\tilde{E}_{pol} = E_{pol}(\mathbf{k}) - E_{pol}(\mathbf{0})$. U is a polariton-polariton interaction potential, N_0 is the concentration of exciton-polaritons in the condensate, A is a normalization area. H_c is the Coulomb repulsion term, $\mathbf{q} = \mathbf{k_1} - \mathbf{k_2}$, where $\mathbf{k_1}$ and $\mathbf{k_2}$ are the momenta of two interacting electrons at the Fermi surface, $q = \sqrt{2k_F(1+\cos\theta)}$. The renormalized bogolon-electron interaction in (1) is given by $M(\mathbf{q})$. It is important that $M(\mathbf{q}) \sim \sqrt{N_0}$. The exciton concentration can be controlled by the external optical pumping, which is why the strength of Cooper coupling in exciton-mediated superconductors may be tuned in large limits.

The effective attraction between two electrons is given by the following expression:

$$V_A(\mathbf{q},\omega) = \frac{2M(\mathbf{q})^2 E_{bog}(\mathbf{q})}{(\hbar\omega)^2 - E^2_{bog}}, \quad (3)$$

where $\hbar\omega = E_{pol}(\mathbf{k_1}+\mathbf{q}) - E_{pol}(\mathbf{k_1})$ is an energy of polariton interchange. The total effective interaction potential including Coulomb repulsion is

$$V_{eff}(\omega) = \frac{A\mathcal{N}}{2\pi}\int_0^{2\pi}[V_A(\mathbf{q},\omega) + V_C(\mathbf{q})]d\theta, \quad (4)$$

where $\mathcal{N} = m_e/\pi\hbar^2$, the Coulomb repulsion is given by $V_C(q) = e^2/2\epsilon A(|\mathbf{q}| + \kappa)$, κ is the screening constant. Eq.(3) shows that the magnitude of the attraction potential increases linearly with N_0. This is illustrated by Fig.2(a), where it is clear that the higher N_0 is, the higher the magnitude is and the larger the attraction region is. On the contrary in Fig.2(b) one can see that the high concentration of electrons leads to the decreasing magnitude of the negative part of potential that corresponds to the attraction between electrons. This effect can be observed in a wide range of polariton concentration values. The only important limitation to this mechanism of SC is the Mott transition from the exciton (exciton-polariton) condensate to the electron-hole plasma. To obtain the critical temperature of the SC phase transition one needs to substitute this potential into the gap

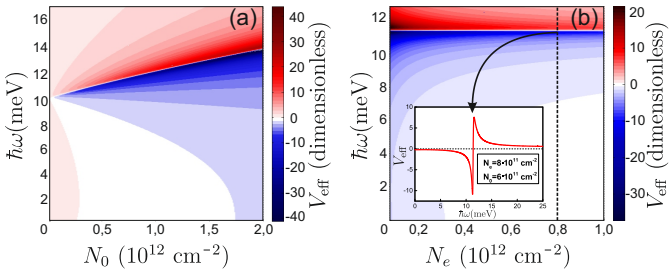

FIG. 2: The magnitude of effective interaction potential as a function of a)concentration of polaritons N_0 and b)concentration of electrons in 2DEG quantum well.Fig(a)is plotted at the constant $N_e = 4\times10^{11}cm^{-2}$ The color shows the magnitude in dimensionless units.Blue region corresponds to the effective attraction between electrons, red region represents the repulsion.The inset presents the profile of the potential at the particular concentration N_e.

equation:

$$\Delta(\omega,\xi)=\int_{-\infty}^{\infty}\frac{U(\xi-\xi')\Delta(\xi',T)\tanh\left(E/2k_BT\right)}{2E}d\xi', \tag{5}$$

where $E=\sqrt{\Delta(\xi',T)^2+\xi'^2}$,U is interaction potential. In the case of a strongly non-monotonous potential $U=V_{eff}(\omega)$ shown in Fig.2 this equation can be solved only numerically. Here we solve it using the iteration method. The example of solution is shown in Fig.3. We assume

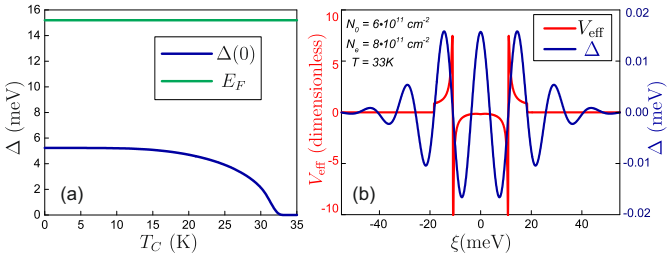

FIG. 3: The results of the solution of the gap-equation. Fig.3 (a) shows $\Delta(0)$ as a function of temperature. The critical temperature T_C in this case is equal to 33K. Fig.3 (b) shows solution of the Eq.(5) at $T=T_C$. The results are presented for the potential with $N_e=8\times10^{11}cm^{-2}$ and $N_0=6\times10^{11}cm^{-2}$

that only electrons that are on the Fermi surface can form Cooper pairs. Here it means that only the point $\Delta(0)$ has a physical meaning. If $\Delta(0)>0$, Cooper pair can be formed. The T_C can be defined as the temperature at which $\Delta(0)$ turns to zero.

Fig.4 represents the critical temperature of the SC transition as a function of the concentration of electrons in a 2DEG QW. The green line shows the temperature that corresponds to the Fermi energy, the other lines represent the dependences of T_C on the concentration of electrons for the concentration of exciton-polaritons fixed at the different levels. One can see that increasing N_e leads to the reduction of the critical temperature. The colored area on the plot shows the range of parameters where our theory is applicable.

We note that our model has two important limitations. First,the thermal energy of electrons at the critical temperature must be lower than the Fermi energy. Otherwise, one cannot assume that electrons obey the Fermi distribution. Also, the absolute value of the gap-energy must be lower than the Fermi-energy. In Fig.4 the area of validity of our approach is limited by $E_F=k_BT$ line. The concentration $N_0=4\times10^{12}cm^{-2}$ is apparently beyond the Mott transition threshold, so that it is unrealistic to expect the high T_C predicted by this line. On the other hand, the exciton concentration $N_0=4\times10^{11}cm^{-2}$ is achievable in realistic GaAs based QW structures, so that crictical temperatures of the order of a few tens of Kelvin must be achievable in semiconductor structures.

The superconducting currents may be observed in our structures until the critical current density is achieved.

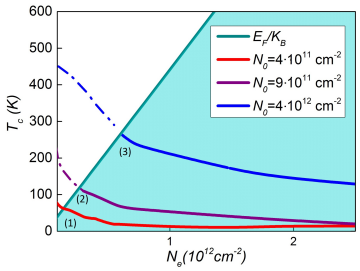

FIG. 4: The dependence of T_C on the concentration of electrons in 2DEG QW, plotted for three different polariton concentrations N_0. Dashed parts of the curves show the region where the theory is not applicable. Red curves (1,2) represents the parameters of the condensate that are achievable in a realistic GaAs-based semiconductor structures.

The critical current density can be conveniently derived from the superconducting gap $\Delta(0)$ as [18]

$$j_c=\frac{eN_e\Delta(0)}{\hbar k_F}, \tag{6}$$

Figure 5(a) shows j_c calculated as a function of the electronic concentration N_e and temperature. One can see that the highest current density appears at the lowest concentrations and lowest temperatures on the graph, that fully agrees with our previous calculations.

Let us discuss now the behaviour of exciton-mediated superconductors in the presence of external magnetic fields. In bulk superconductors, the Meissner effect exists until the critical magnetic field achieved. This field is linked to the critical current. Namely, the critical field induces a surface current equal to j_c. At the critical field the superconducting gap is different from zero. In our case, the superconducting layer is much thinner than the typical penetration length of the magnetic field into the superconductor. The superconductivity is still suppressed by the magnetic field in this case, but the gap vanishes at the critical field B_{cr}[19],that can be found from the condition:

$$\Delta(0,B_{cr})=0, \tag{7}$$

In order to find B_{cr}, we will account for the magnetic field in the gap equation. The field affects the radius of the Fermi circle making it larger because of the decrease of the density of electronic states in a two-dimensional layer. A minor effect is the modification of electron-exciton interaction potential due to the shrinkage of the exciton Bohr radius. To account for the magnetic field effect on k_F, we use the expression for the radii of the circles in the reciprocal space, that correspond to Landau levels in

the quasiclassical approximation[20].

$$k_p^2 = (p + \frac{1}{2})\frac{2eB}{\hbar c}, p = 0, 1, 2... \quad (8)$$

Electrons may occupy quantum states in the Γ vicinity of these circles, where Γ is the Dingle broadening of Landau levels dependent on the structural disorder and scattering processes. The area occupied by electrons in the reciprocal space at each circle at zero temperature can be found as

$$S_p = 2\pi k_p \delta k_p \quad (9)$$

where $\delta k_p = \frac{2m\Gamma}{\hbar^2 k_p}$. The Fermi wave vector can be expressed as $k_F = k_M$, where the index M can be found from the condition:

$$\frac{2}{(2\pi)^2}\sum_{p=0}^{M-1} S_p < N_e \leq \frac{2}{(2\pi)^2}\sum_{p=0}^{M} S_p \quad (10)$$

Fig.5(b) shows k_F and T_c as functions of magnetic field B for the fixed electron and polariton densities. All parameters are the same that we used for potential calculation for GaAs-structure. In this case $N_e = 8 \times 10^{11} cm^{-2}, N_0 = 6^{\times} 10^{11} cm^{-2}$,The Dingle broadening of Landau Levels is taken to be to $0.3meV$. At low magnetic fields given by a condition $\hbar\omega_c < \Gamma$ we assume that $k_F = k_F(B = 0)$, neglecting the weak oscillations of k_F due to the oscillating electron density of states[21]. Our

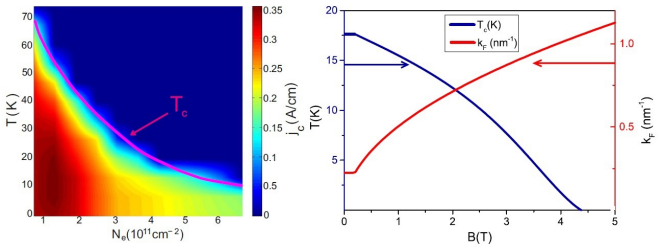

FIG. 5: (a) The dependence of the critical current j_c on the temperature and electron concentration. (b)Fermi wavevector (red curve) and critical temperature(blue curve) as a function of magnetic field B.$N_e = 8 \times 10^{11} cm^{-2}$.The Dingle broadening of Landau Levels Γ is taken to be 0.3 meV, that corresponds to the cyclotron energy $\hbar\omega_c$ at B=0.2T.

calculation shows that the increase of B at a constant Γ leads to the strong increase of the Fermi wave vector, which is why the critical temperature decreases and eventually vanishes at $B_c \approx 4T$. The increase of k_F accounts for the reduction of the effective area occupied by each electron in the real space due to the cyclotron motion. We note, that the validity of the quasi-classical approximation is limited at strong quantising magnetic fields. In our case, the number of occupied Landau levels is over 10 even at $B \approx 4T$, which allows considering the quasiclassical result as a trustworthy approximation. Other effects which may influence B_c include the electron Zeeman splitting and edge current effects, which are beyond the scope of the present work.

In conclusion, multilayer semiconductor heterostructures appear to be promising candidates for the observation of exciton-mediated superconductivity. Contrary to the previous expectations, fully semiconductor structures, combining doped and undoped quantum wells provide higher critical temperatures than metal-semiconductor structures. This can be explained by the fact that exciton-mediated attraction weakens with the increasing of the Fermi energy faster than the Coulomb repulsion does. In the absence of magnetic field we predict the critical temperatures of the order of 50K in realistic GaAs-based microcavities. We show that external magnetic fields suppress superconductivity in thin semiconductor layers due to the increase of the Fermi wavevector.

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[1] J. Bardeen, L. N. Cooper, and J. R. Schrieffer, Phys. Rev. **106**, 162 (1957), URL http://link.aps.org/doi/10.1103/PhysRev.106.162.

[2] W. A. Little, Phys. Rev. **134**, A1416 (1964), URL http://link.aps.org/doi/10.1103/PhysRev.134.A1416.

[3] V. L. Ginzburg, *On Superconductivity and Superfluidity* (Springer, 2009).

[4] P. Morel and P. W. Anderson, Phys. Rev. **125**, 1263 (1962), URL http://link.aps.org/doi/10.1103/PhysRev.125.1263.

[5] V. L. Ginzburg, Physics-Uspekhi **13**, 335 (1970), URL http://ufn.ru/en/articles/1970/3/c/.

[6] V. L. Ginzburg, Physics-Uspekhi **19**, 174 (1976), URL http://ufn.ru/en/articles/1976/2/f/.

[7] J. Bauer, J. E. Han, and O. Gunnarsson, Phys. Rev. B **87**, 054507 (2013), URL http://link.aps.org/doi/10.1103/PhysRevB.87.054507.

[8] C. Aruta, G. Ghiringhelli, C. Dallera, F. Fracassi, P. G. Medaglia, A. Tebano, N. B. Brookes, L. Braicovich, and G. Balestrino, Phys. Rev. B **78**, 205120 (2008), URL http://link.aps.org/doi/10.1103/PhysRevB.78.205120.

[9] A. Gozar, G. Logvenov, L. F. Kourkoutis, A. T. Bollinger, L. A. Giannuzzi, D. A. Muller, and I. Bozovic, Nature **455**, 782 (2008), ISSN 0028-0836, URL http://dx.doi.org/10.1038/nature07293.

[10] F. P. Laussy, A. V. Kavokin, and I. A. Shelykh, Phys. Rev. Lett. **104**, 106402 (2010), URL http://link.aps.org/doi/10.1103/PhysRevLett.104.106402.

[11] F. P. Laussy, T. Taylor, I. A. Shelykh, and A. V. Kavokin, Journal of Nanophotonics **6**, 064502 (2012), URL http://dx.doi.org/10.1117/1.JNP.6.064502.

[12] A. V. Kavokin, J. J. Baumberg, G. Malpuech, and F. P. Laussy, *Microcavities* (Oxford University Press, New York, 2007).

[13] A. Imamoglu, R. J. Ram, S. Pau, and Y. Yamamoto, Phys. Rev. A **53**, 4250 (1996).

[14] H. Deng, H. Haug, and Y. Yamamoto, Rev. Mod. Phys. **82**, 1489 (2010), URL http://link.aps.org/doi/10.1103/RevModPhys.82.1489.

[15] J. D. Plumhof, T. Stferle, L. Mai, U. Scherf, and R. F. Mahrt, Nat Mater **13**, 247 (2014), ISSN 1476-1122, URL http://dx.doi.org/10.1038/nmat3825.

[16] S. Christopoulos, G. B. H. von Högersthal, A. J. D. Grundy, P. G. Lagoudakis, A. V. Kavokin, J. J. Baumberg, G. Christmann, R. Butté, E. Feltin, J.-F. Carlin, et al., Phys. Rev. Lett. **98**, 126405 (2007), URL http://link.aps.org/doi/10.1103/PhysRevLett.98.126405.

[17] J. J. Baumberg, A. V. Kavokin, S. Christopoulos, A. J. D. Grundy, R. Butté, G. Christmann, D. D. Solnyshkov, G. Malpuech, G. Baldassarri Höger von Högersthal, E. Feltin, et al., Phys. Rev. Lett. **101**, 136409 (2008), URL http://link.aps.org/doi/10.1103/PhysRevLett.101.136409.

[18] H.Ibach and H. Luth, *Solid State Physics* (Springer, Berlin, 1996).

[19] D. H. Douglass, Phys. Rev. Lett. **6**, 346 (1961), URL http://link.aps.org/doi/10.1103/PhysRevLett.6.346.

[20] L. D. Landau and E. L. Lifshitz, *Quantum Mechanics: Non-Relativistic Theory.* (Pergamon Press., 1977).

[21] T. Champel and V. P. Mineev, Philosophical Magazine Part B **81**, 55 (2001).